SURFACE MOUNT FAST SWITCHING DIODE

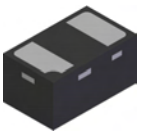
Features

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance
- **Lead Free by Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X1-DFN1006-2
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Marking Information
- Terminals: Finish - NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

X1-DFN1006-2



Bottom View

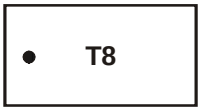
Ordering Information (Note 3)

Part Number	Case	Packaging
1N4448HLP-7	X1-DFN1006-2	3,000/Tape & Reel
1N4448HLP-7B	X1-DFN1006-2	10,000/Tape & Reel

Notes: 1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
3. For packaging details, go to our website at http://www.diodes.com.

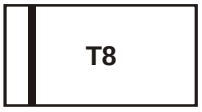
Marking Information

1N4448HLP-7



Top View
Dot Denotes
Cathode Side

1N4448HLP-7B



Top View
Bar Denotes
Cathode Side

T8 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage		V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V_{RRM} V_{RWM} V_R	80	V
RMS Reverse Voltage		$V_{R(RMS)}$	57	V
Forward Continuous Current		I_{FM}	250	mA
Average Rectified Output Current		I_O	125	mA
Non-Repetitive Peak Forward Surge Current	@ t = 1.0μs @ t = 1.0s	I_{FSM}	2.0 1.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	250	mW
Thermal Resistance Junction to Ambient (Note 4)	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-65 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Conditions
Reverse Breakdown Voltage (Note 5)	$V_{(BR)R}$	80	—	V	I_R = 100μA
Forward Voltage	V_F	0.62 — — —	0.72 0.855 1.0 1.25	V	I_F = 5.0mA I_F = 10mA I_F = 100mA I_F = 150mA
Peak Reverse Current (Note 5)	I_R	—	100 50 30 25	nA μA μA nA	V_R = 80V V_R = 75V, T_J = 150°C V_R = 25V, T_J = 150°C V_R = 20V
Total Capacitance	C_T	—	3.0	pF	V_R = 0.5V, f = 1.0MHz
Reverse Recovery Time	t_{rr}	—	4.0	ns	I_F = I_R = 10mA, I_{rr} = 0.1 x I_R, R_L = 100Ω

Notes: 4. Part mounted on FR-4 PC board with recommended pad layout, which can be found on our website at http://www.diodes.com.
5. Short duration pulse test used to minimize self-heating effect.

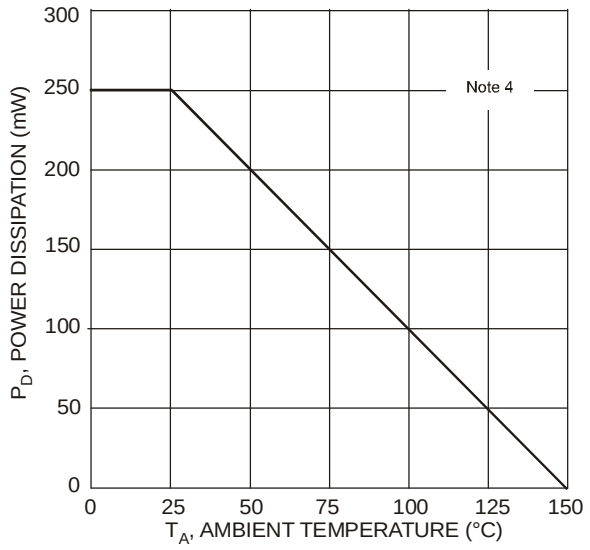


Fig. 1 Power Derating Curve

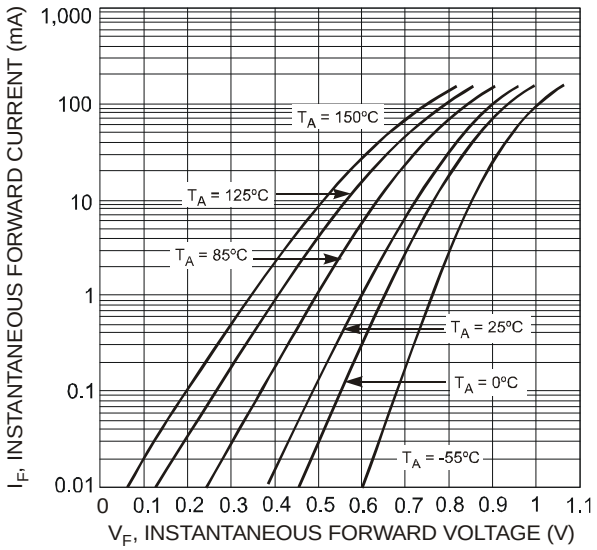


Fig. 2 Typical Forward Characteristics

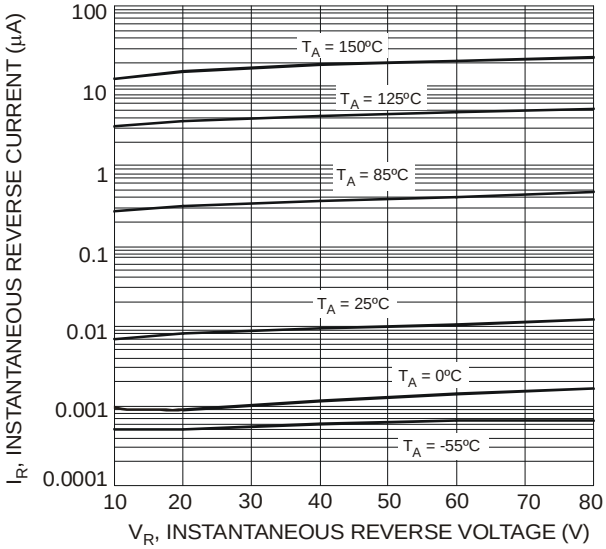


Fig. 3 Typical Reverse Characteristics

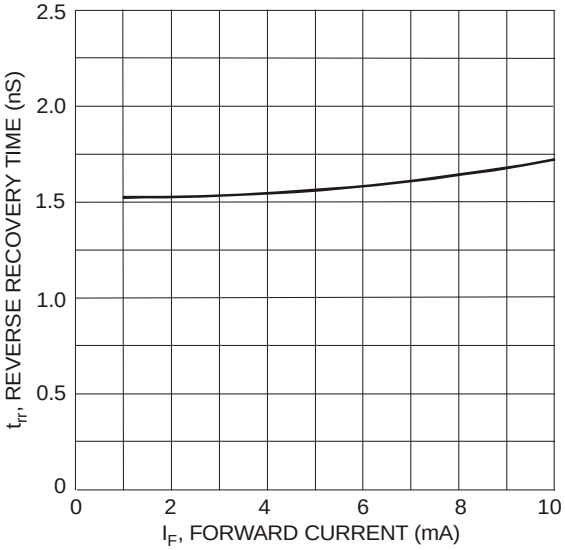
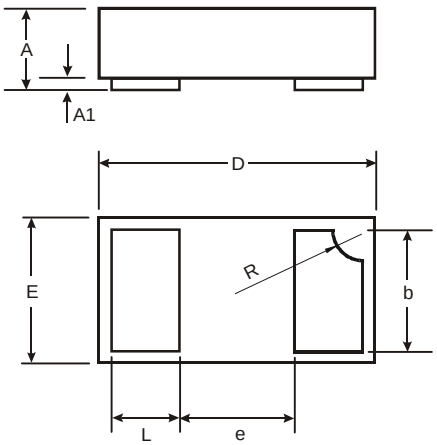


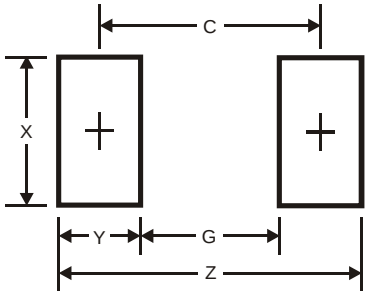
Fig. 4 Reverse Recovery Time vs. Forward Current

Package Outline Dimensions



X1-DFN1006-2			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.03
b	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.40
L	0.20	0.30	0.25
R	0.05	0.15	0.10
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G	0.3
X	0.7
Y	0.4
C	0.7